

FIG. 1 (PRIOR ART)

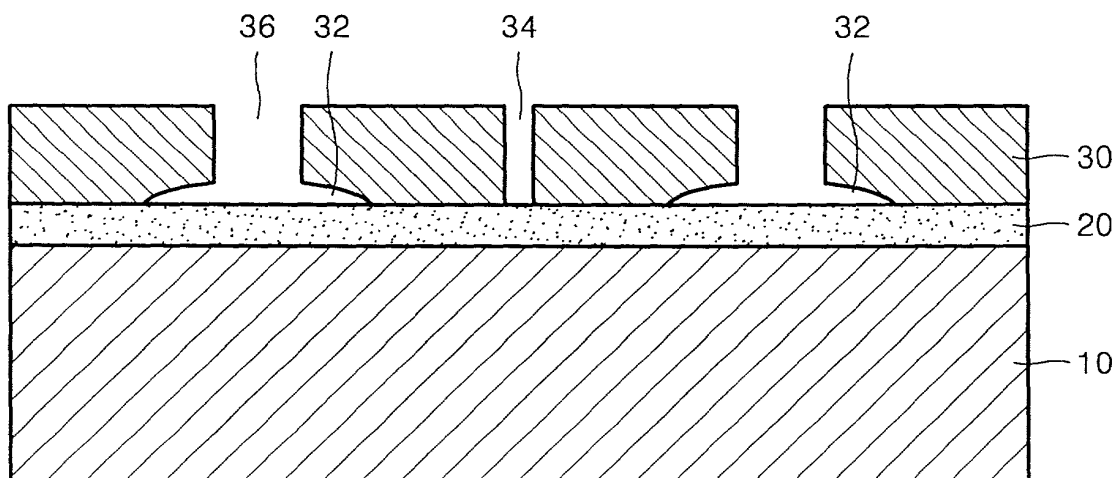


Figure 1 is a perspective view of a semiconductor device. The device includes a substrate 100, a thin layer 200, and a patterned layer 210. The patterned layer 210 defines a central region 300 and four peripheral regions 310. The central region 300 contains four square openings. The peripheral regions 310 are raised relative to the central region 300. Section lines III-III' and III'-III' are indicated.

FIG. 4A

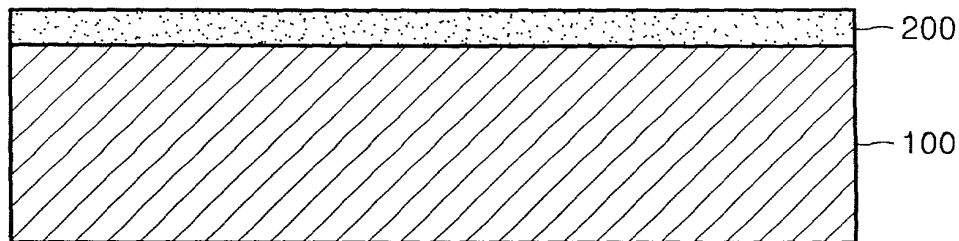


FIG. 4B

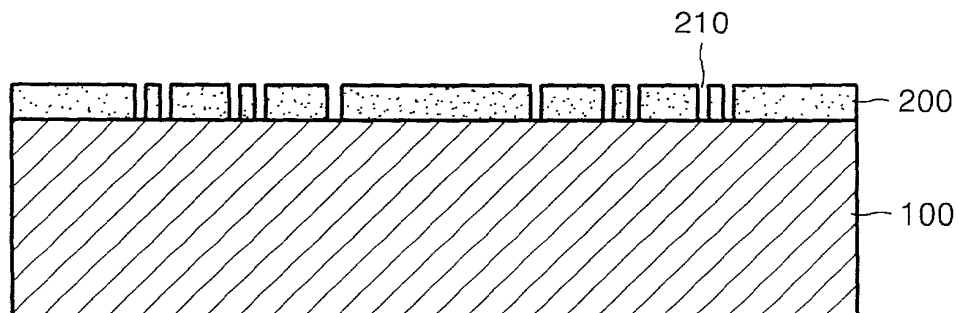


FIG. 4C

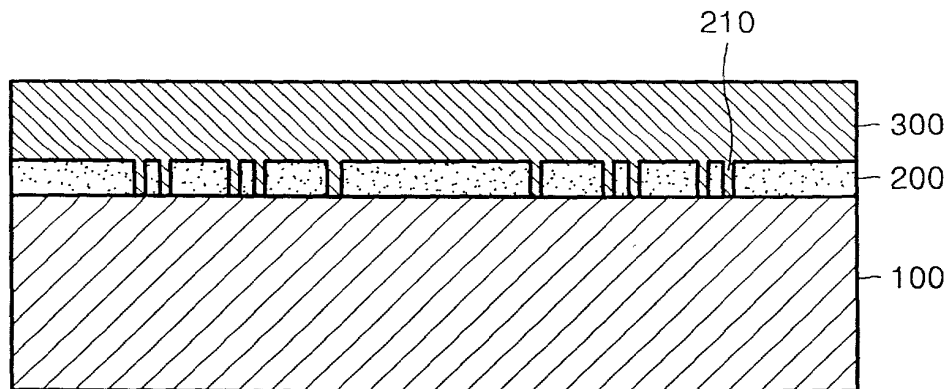


FIG. 4D

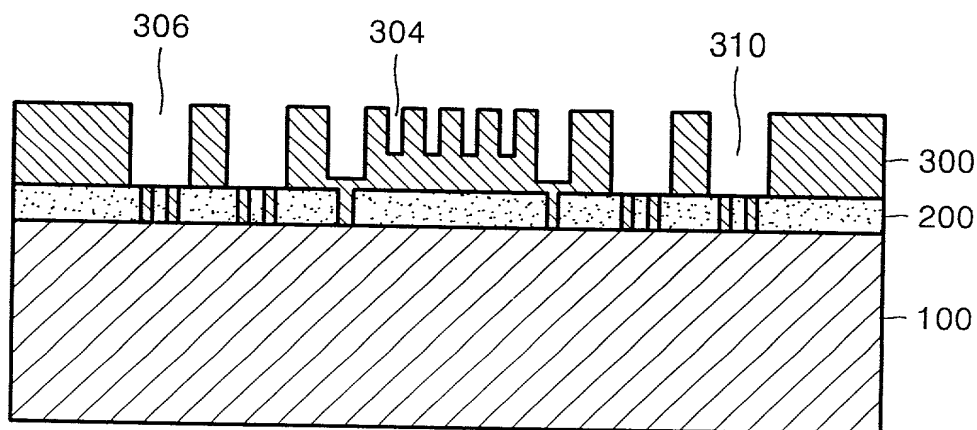


FIG. 4E

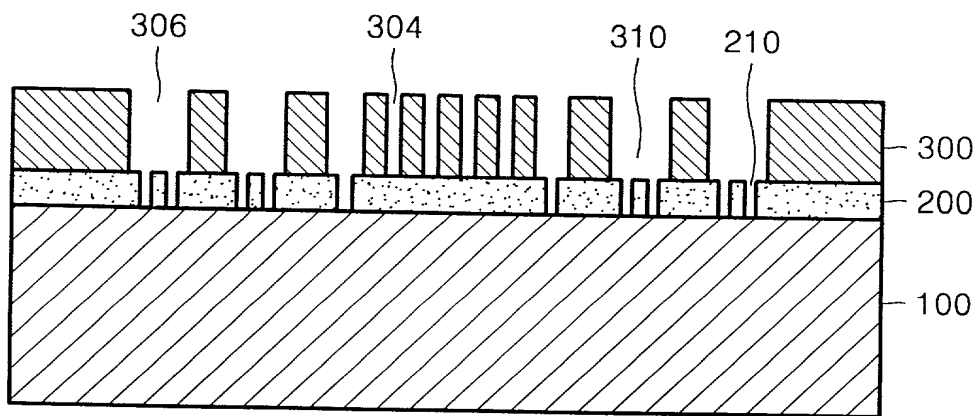


FIG. 5 (PRIOR ART)

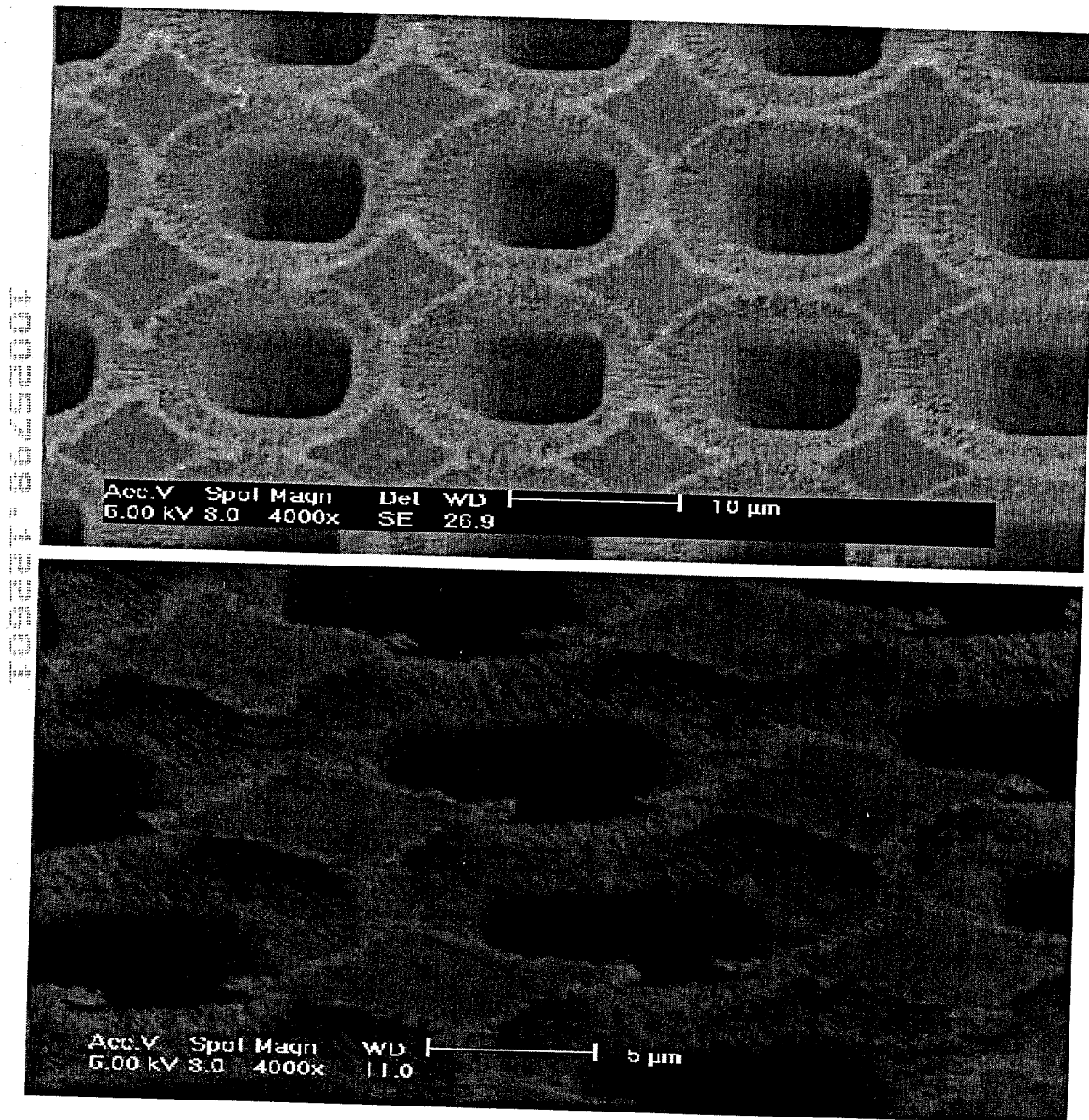
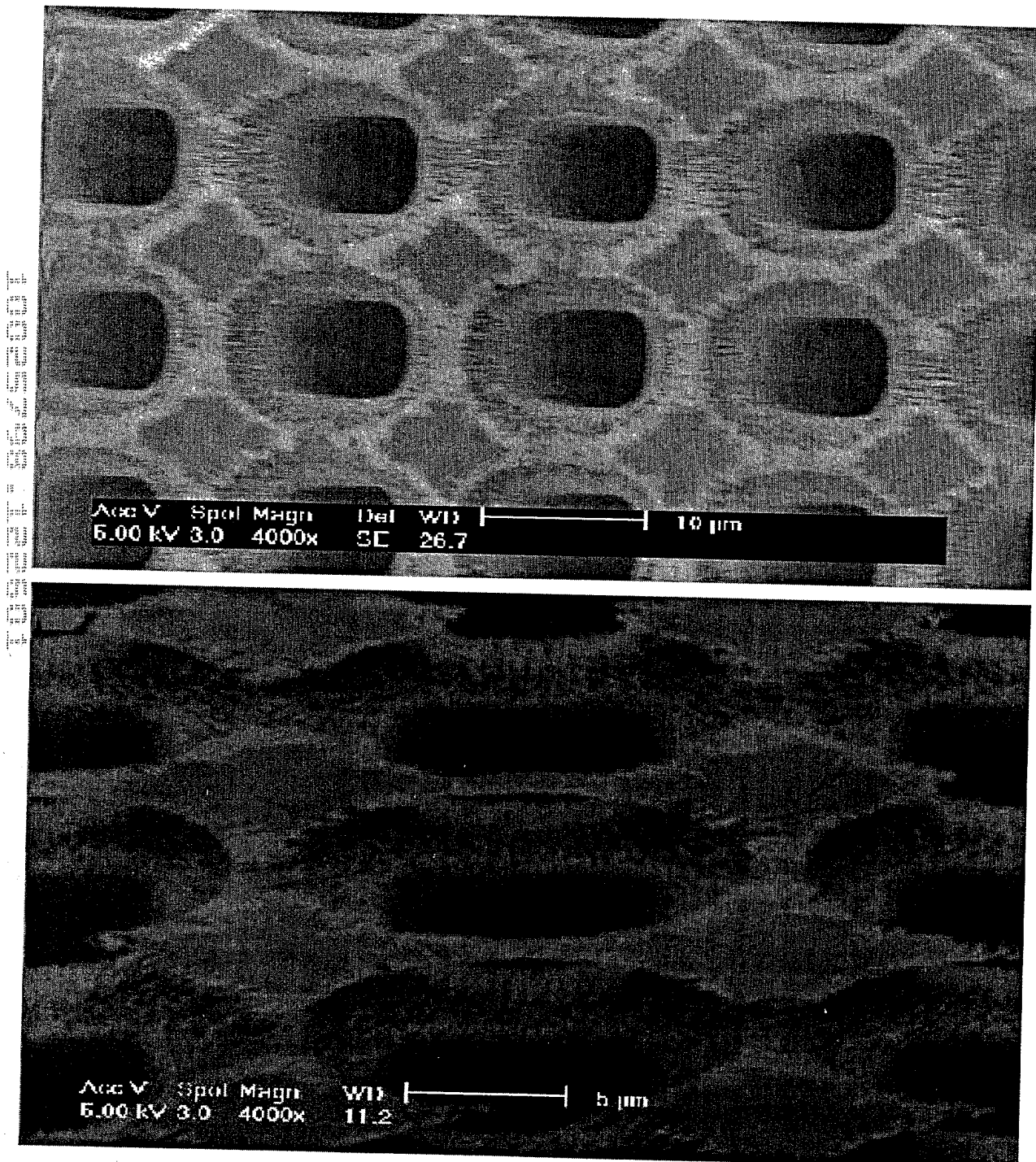
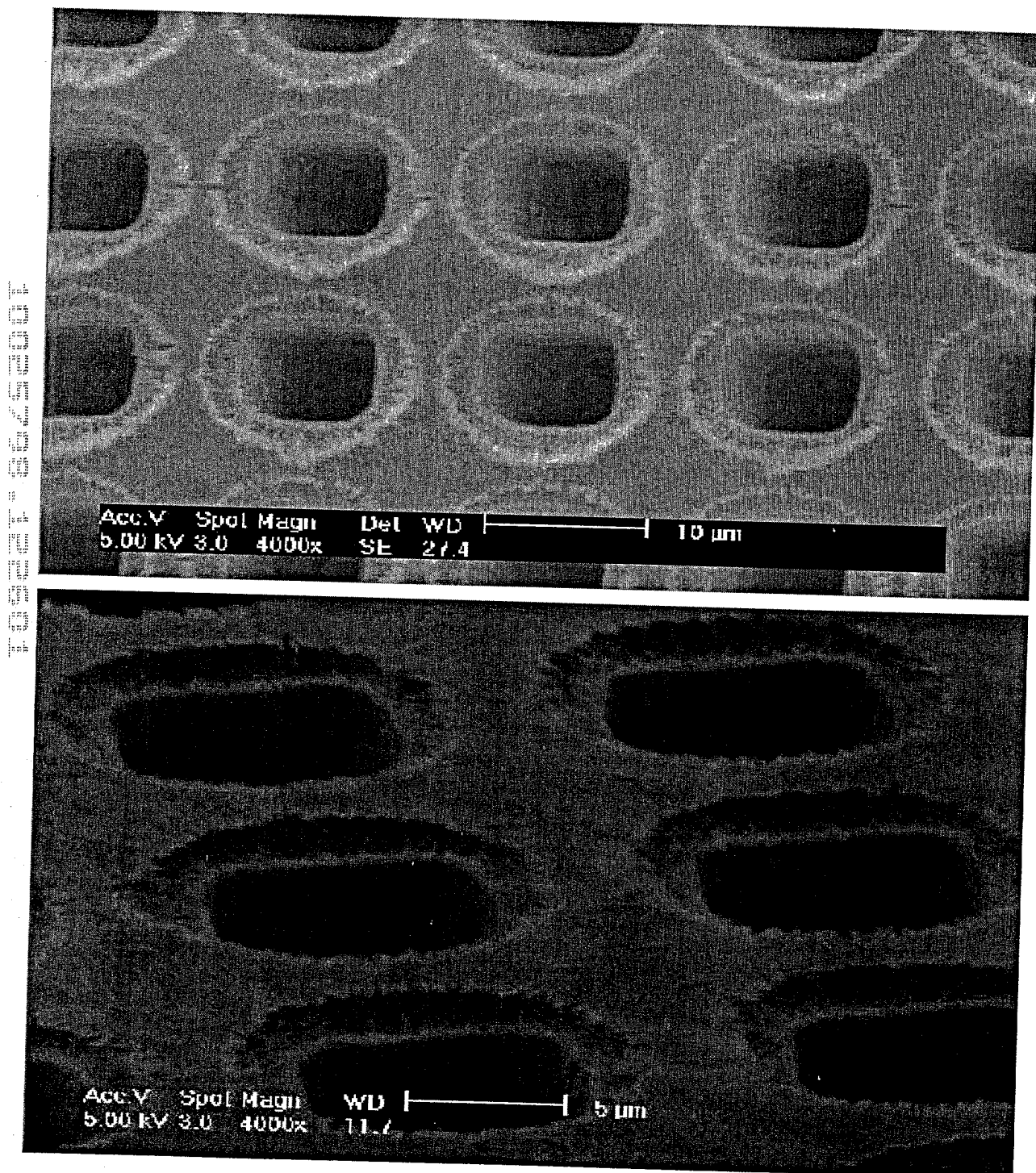


FIG. 6



APPLN. FILING DATE: DECEMBER 26, 2001
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FIG. 7



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